



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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1214-32L

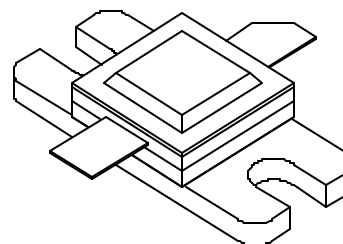
32 Watts, 36 Volts
Pulsed Radar at 1.2-1.4 GHz

GENERAL DESCRIPTION

The 1214-32L is an internally matched, COMMON BASE transistor capable of providing 32 Watts of pulsed RF output power at 5 milliseconds pulse width, 20% duty factor across the band 1200 to 1400 MHz. This hermetically solder-sealed transistor is specifically designed for LBand radar applications. It utilizes gold metallization and diffused emitter ballasting to provide high reliability and supreme ruggedness.

CASE OUTLINE

55AW-1



ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

Device Dissipation @ 25°C¹ 125 W

Maximum Voltage and Current

Collector to Base Voltage (BV_{ces}) 50 V

Emitter to Base Voltage (BV_{ebo}) 3.5 V

Collector Current (I_c) 5 A

Maximum Temperatures

Storage Temperature -65 to +200 °C

Operating Junction Temperature +200 °C

ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out} ¹	Power Output	F = 1200-1400 MHz	32		41	W
P _g	Power Gain	Pin = 5.3 W	7.8		8.9	dB
η _c	Collector Efficiency	Pulse Width = 5 mS	42	45		%
R _L	Return Loss	Duty Factor = 20%	-9			dB
Pd	Pulse Droop				0.5	dB
VSWR ¹	Load Mismatch Tolerance ¹	F=1200 MHz, Pin=5.3 W			3.0:1	

FUNCTIONAL CHARACTERISTICS @ 25°C

BV _{ebo}	Emitter to Base Breakdown	I _e = 15 mA	3.5			V
BV _{ces}	Collector to Emitter Breakdown	I _c = 100 mA	50			V
h _{FE}	DC – Current Gain	V _{ce} = 5V, I _c = 1A	20			
θ _{jc} ¹	Thermal Resistance				1.4	°C/W

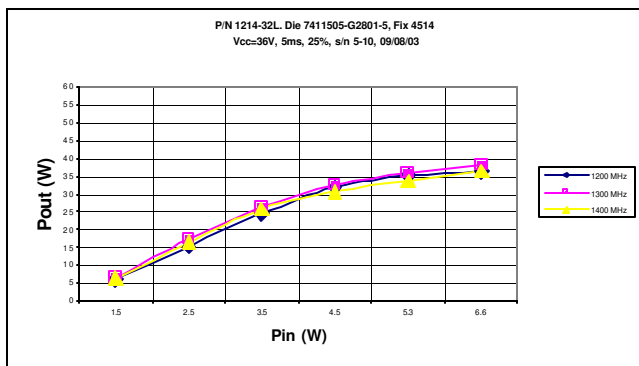
NOTES: 1. Pulse condition of 5 mS, 20%

Rel 5: March 2005

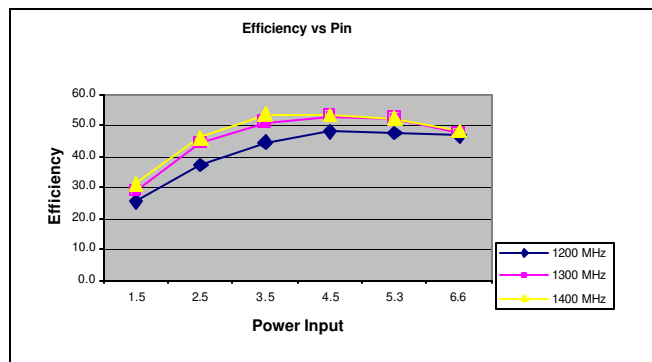
1214-32L

Performance Curves

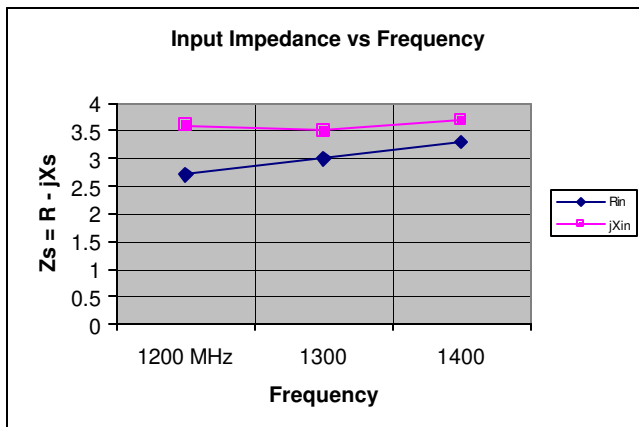
Power Output vs Power Input



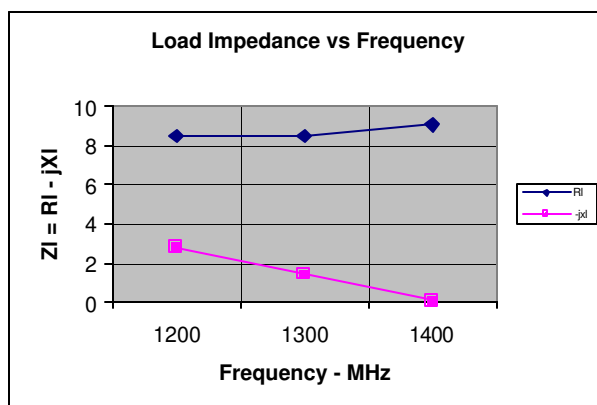
Efficiency vs Power Input



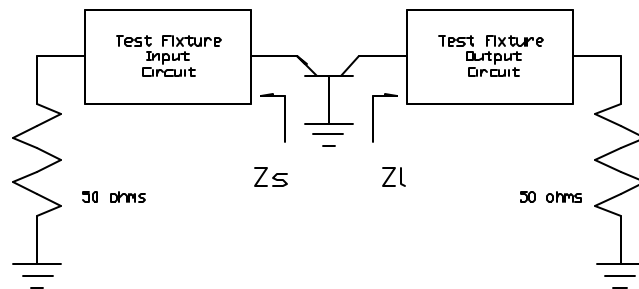
Input Impedance

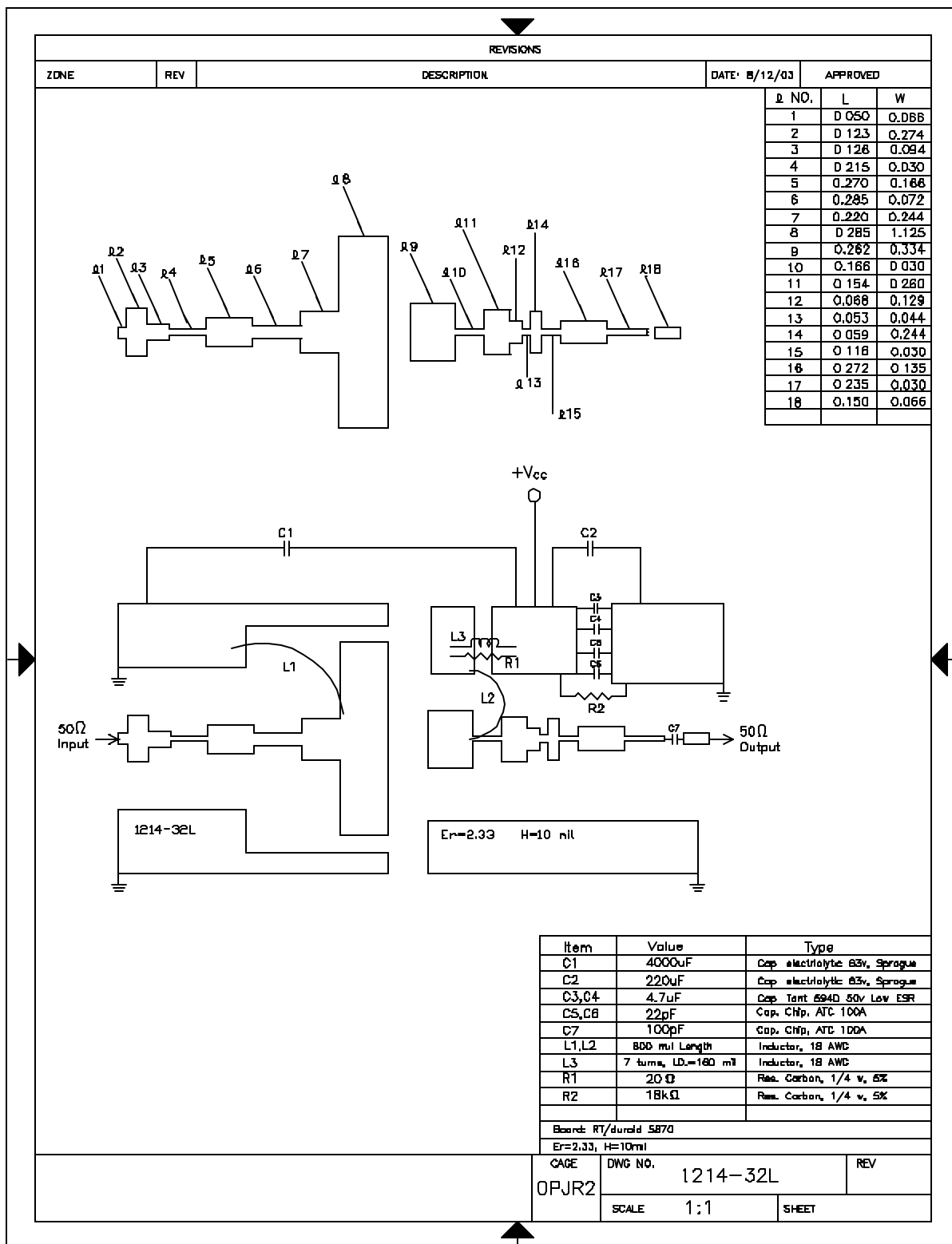


Load Impedance



Impedance		
Freq	Zs	Zl
1200	2.7-j3.6	8.5-j2.8
1300	3-j3.5	8.5-j1.44
1400	3.3-j3.7	9.07-j0.08





1214-32L

